



STS4DPFS30L

P-CHANNEL 30V - 0.045Ω - 5A SO-8 STripFET™ MOSFET PLUS SCHOTTKY RECTIFIER

Table 1: General Features

MOSFET TYPE	V _{DSS}	R _{DS(on)}	I _D
STS4DPFS30L	30 V	< 0.055 Ω	5 A
SCHOTTKY	I _{F(AV)}	V _{RRM}	V _{F(MAX)}
	3 A	30 V	0.51 V

- TYPICAL R_{DS(on)} = 0.045 Ω
- CONDUCTION LOSSES REDUCED
- SWITCHING LOSSES REDUCED
- LOW THRESHOLD DRIVE
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY

DESCRIPTION

This MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- DC/DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT
- POWER MANAGEMENT IN CELLULAR PHONES
- DC MOTOR DRIVE

Figure 1: Package

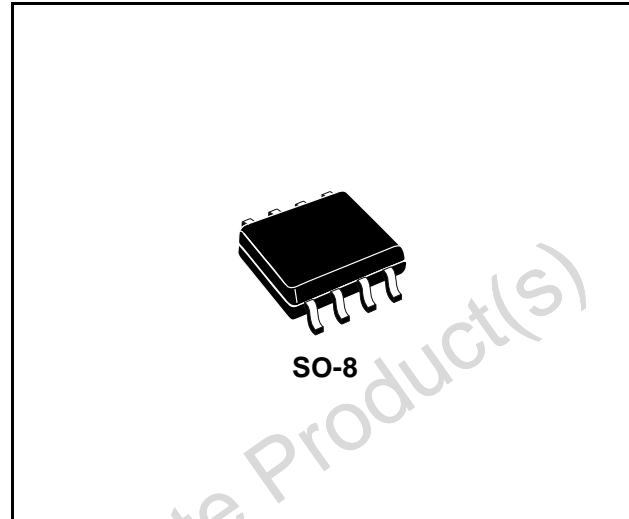


Figure 2: Internal Schematic Diagram

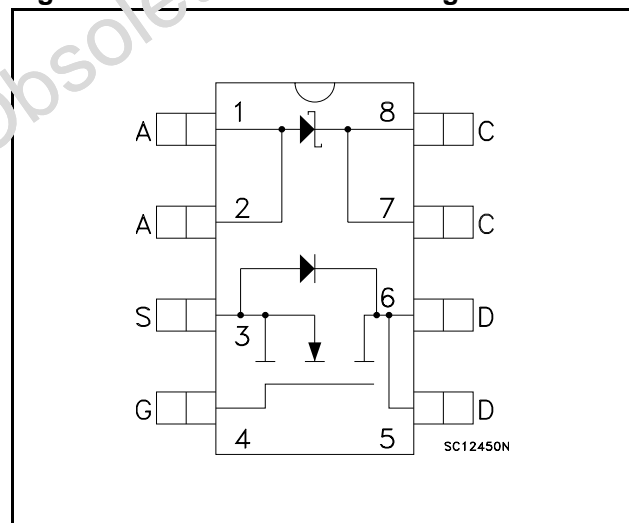


Table 2: Order Codes

PART NUMBER	MARKING	PACKAGE	PACKAGING
STS4DPF30L	4DFS30L	SO-8	TAPE & REEL

Table 3: MOSFET Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C Single Operating	5	A
I _D	Drain Current (continuous) at T _C = 100°C Single Operating	4	A
I _{DM} (•)	Drain Current (pulsed)	20	A
P _{TOT}	Total Dissipation at T _C = 25°C Single Operating	2.5	W
T _j T _{stg}	Operating Junction Temperature Storage Temperature	150 -55 to 150	°C °C

(•) Pulse width limited by safe operating area

Note: For the P-CHANNEL MOSFET actual polarity of voltages and current has to be reversed

Table 4: Schottky Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	30	V
I _{F(RMS)}	RMS Forward Current	20	A
I _{F(AV)}	Average Forward Current	TL = 125°C δ = 0.5	3 A
I _{FSM}	Surge Non Repetitive Forward Current	tp = 10 ms Sinusoidal	75 A
I _{RRM}	Repetitive Peak Reverse Current	tp = 2 μs F = 1 kHz	1 A
I _{RSM}	Non Repetitive Peak Reverse Current	tp = 100 μs	1 A
dv/dt	Critical Rate Of Rise Of Reverse Voltage	10000	V/μs

Table 5: Thermal Data

R _{thj-case}	Thermal Resistance Junction-case Single Operating	50	°C/W
R _{thj-amb}	(*)Thermal Resistance Junction-ambient SCHOTTKY	100	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300	°C

(*) Mounted on FR-4 board (Steady State)

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)

Table 6: On/Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 2.5 A V _{GS} = 4.5 V, I _D = 2.5 A		0.045 0.065	0.055 0.075	Ω Ω

ELECTRICAL CHARACTERISTICS(CONTINUED)**Table 7: Dynamic**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} = 15\text{ V}$, $I_D = 2.5\text{ A}$		10		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		1350 490 130		pF pF pF

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5%**Table 8: Switching On**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 15\text{ V}$, $I_D = 2.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (see Figure 16))		25 35		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 24\text{ V}$, $I_D = 5\text{ A}$, $V_{GS} = 5\text{ V}$ (see, Figure 19)		12.5 5 3	16	nC nC nC

Table 9: Switching Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 15\text{ V}$, $I_D = 2.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ (see, Figure 16)		125 35		ns ns

Table 10: Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				5	A
I_{SDM} (2)	Source-drain Current (pulsed)				20	A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0$			1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$, $T_J = 150^\circ\text{C}$ (see, Figure 17)		45 36 1.6		ns nC A

Table 11: Schottky Static Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_R (*)	Reversed Leakage Current	$T_J = 25^\circ\text{C}$, $V_R = 30\text{ V}$ $T_J = 125^\circ\text{C}$, $V_R = 30\text{ V}$		0.03	0.2 100	mA mA
V_F (*)	Forward Voltage Drop	$T_J = 25^\circ\text{C}$, $I_F = 3\text{ A}$ $T_J = 125^\circ\text{C}$, $I_F = 3\text{ A}$		0.46	0.51 0.46	V V

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

Figure 3: Safe Operating

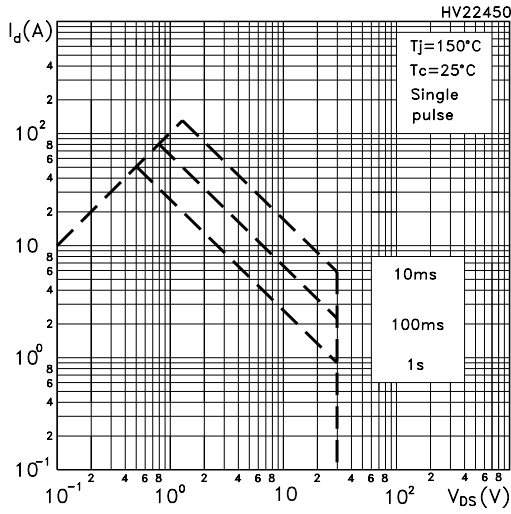


Figure 4: Output Characteristics

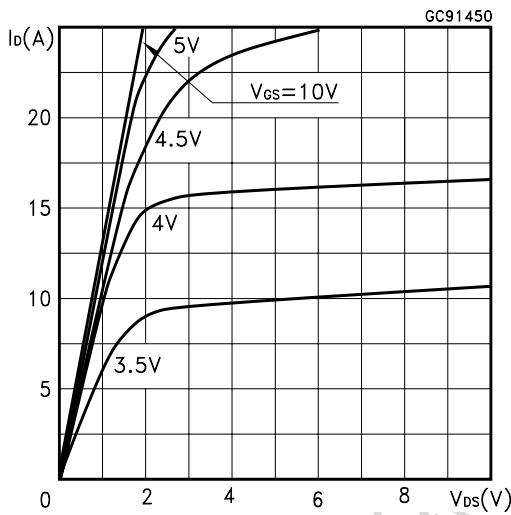


Figure 5: Transconductance

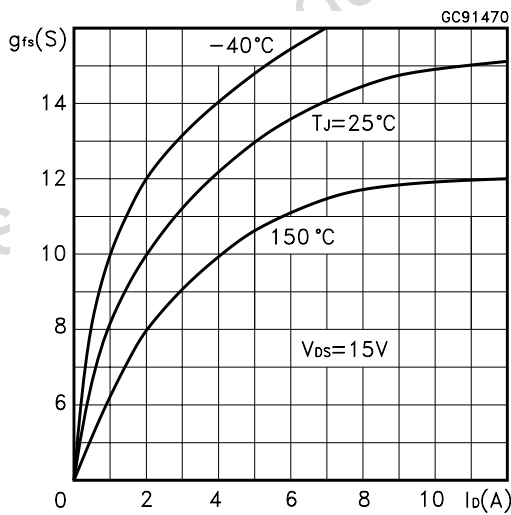


Figure 6: Thermal Impedance

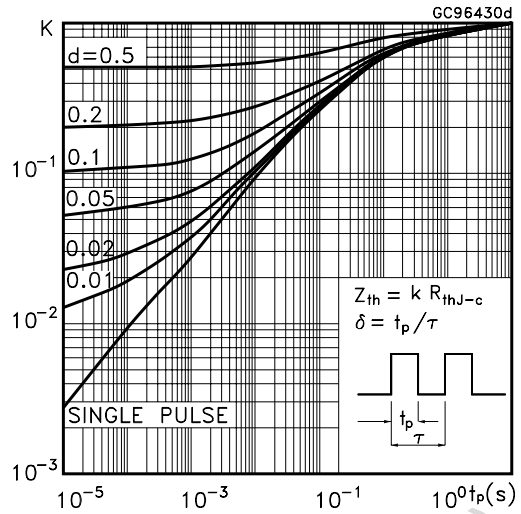


Figure 7: Transfer Characteristics

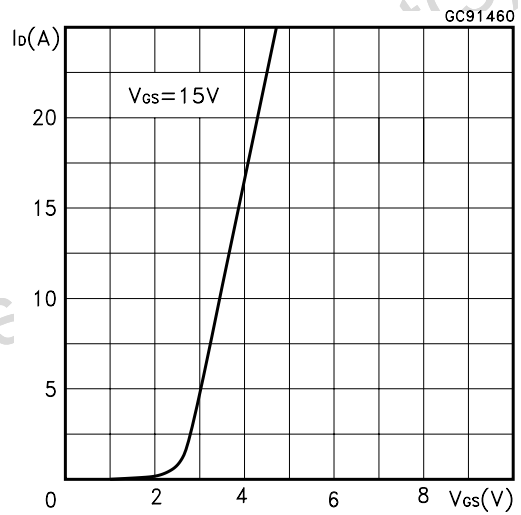


Figure 8: Static Drain-Source On Resistance

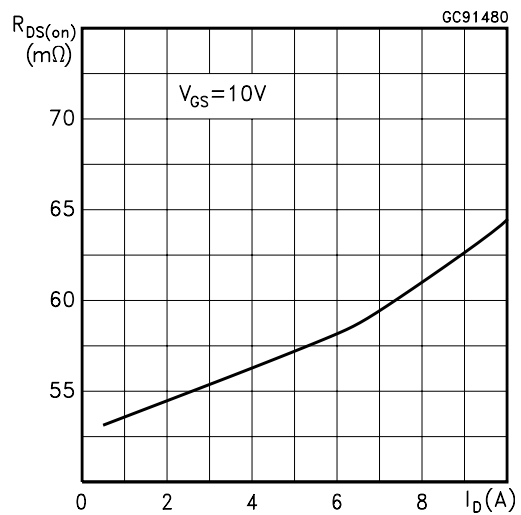


Figure 9: Gate Charge vs Gate-Source Voltage

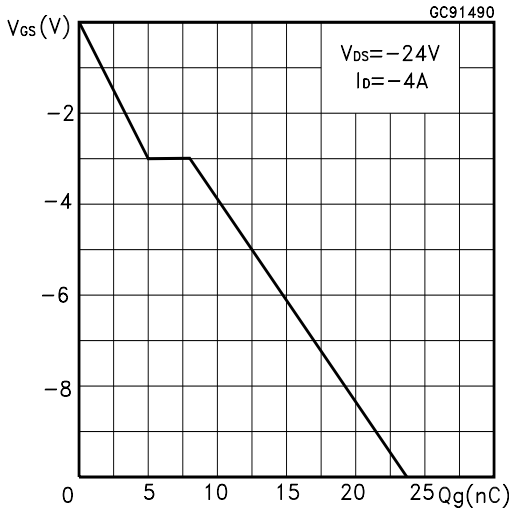


Figure 10: Normalized Gate Threshold Voltage vs Temperature

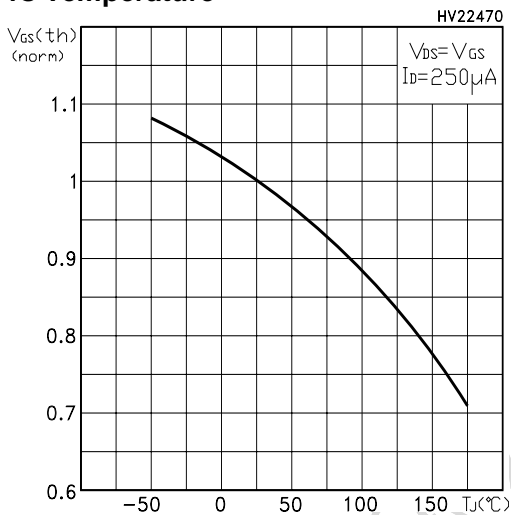


Figure 11: Source-Drain Diode Forward Characteristics

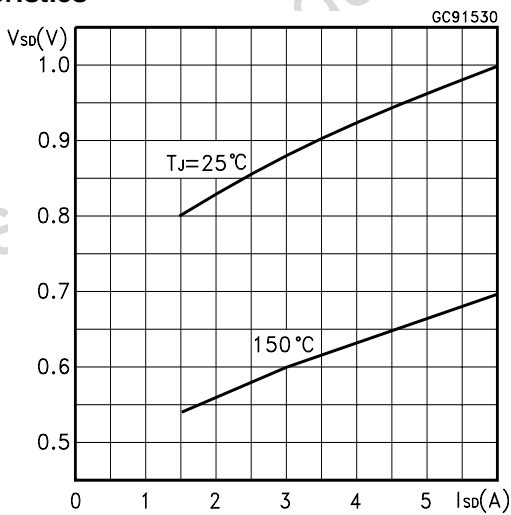


Figure 12: Capacitances Variations

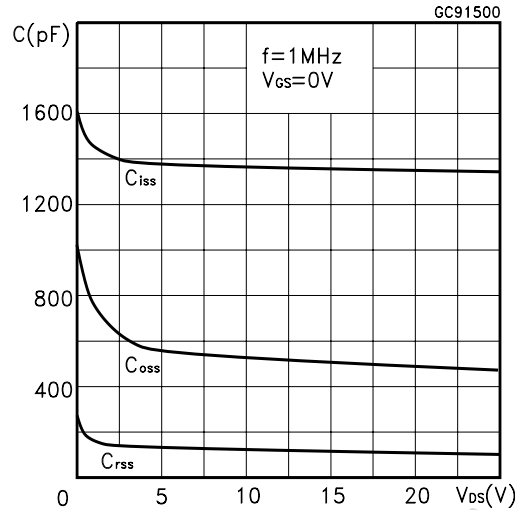


Figure 13: Normalized On Resistance vs Temperature

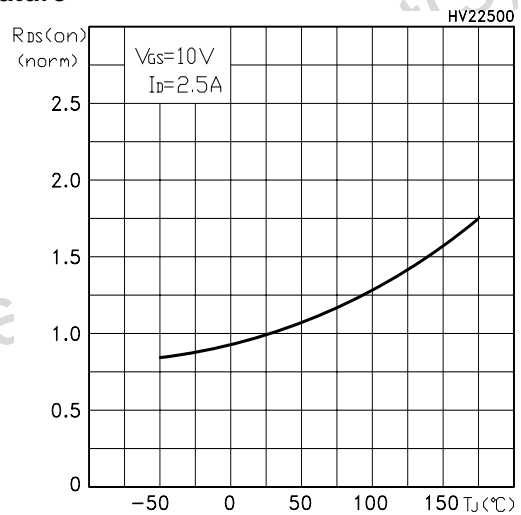


Figure 14: Normalized BVdss vs Temperature

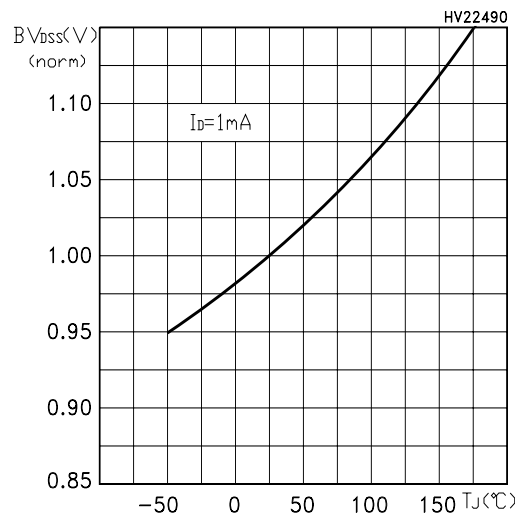


Figure 15: Unclamped Inductive Load Test Circuit

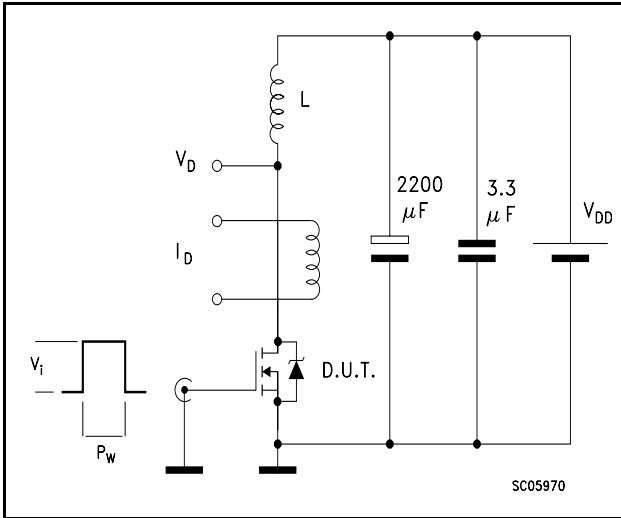


Figure 16: Switching Times Test Circuit For Resistive Load

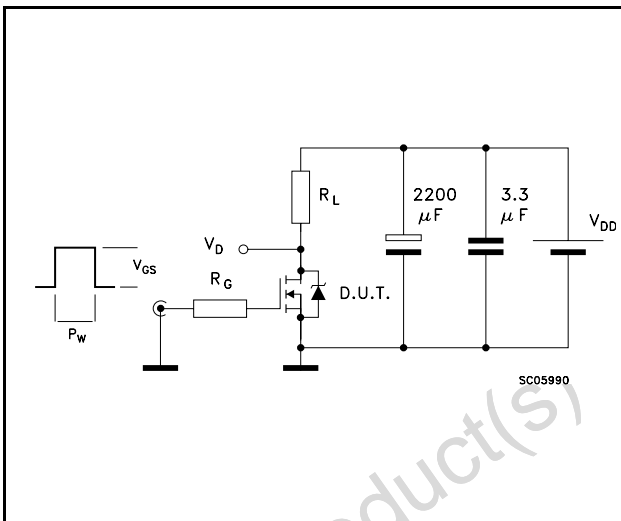


Figure 17: Test Circuit For Inductive Load Switching and Diode Recovery Times

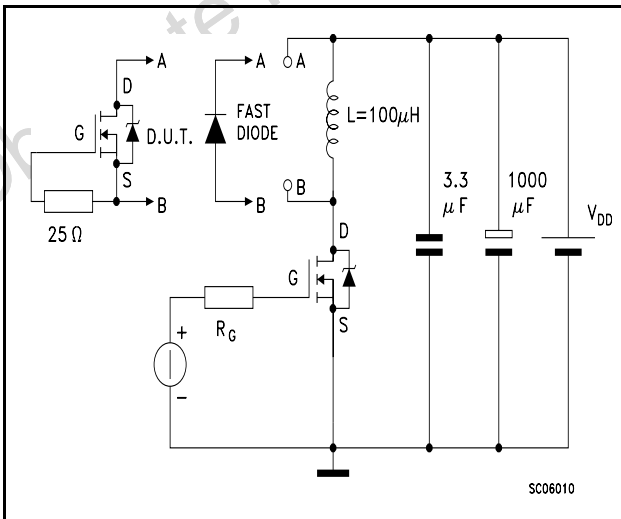


Figure 18: Unclamped Inductive Waform

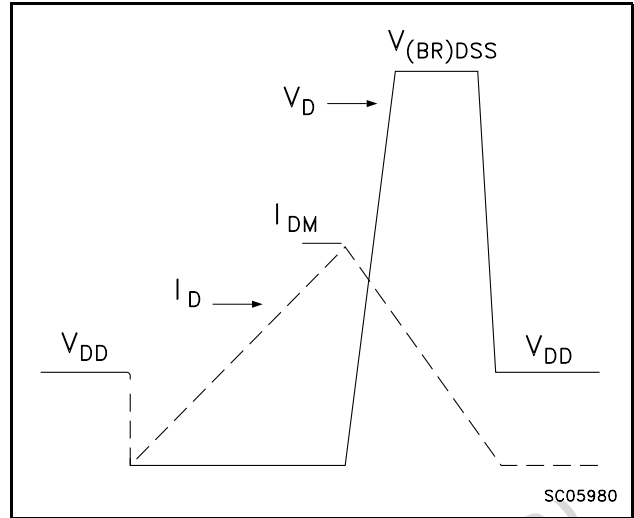
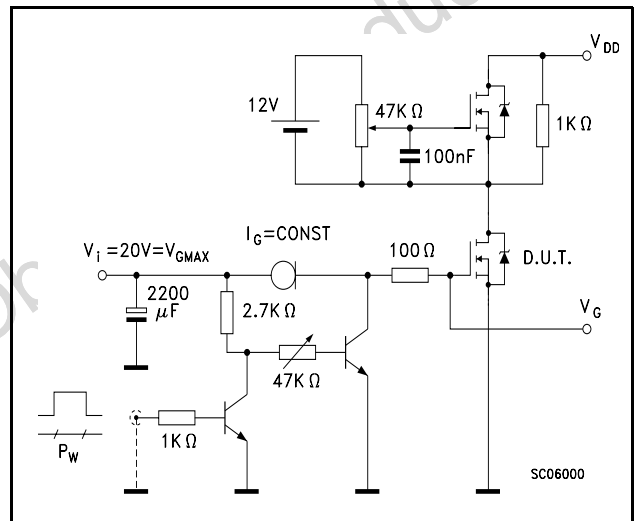


Figure 19: Gate Charge Test Circuit



SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					

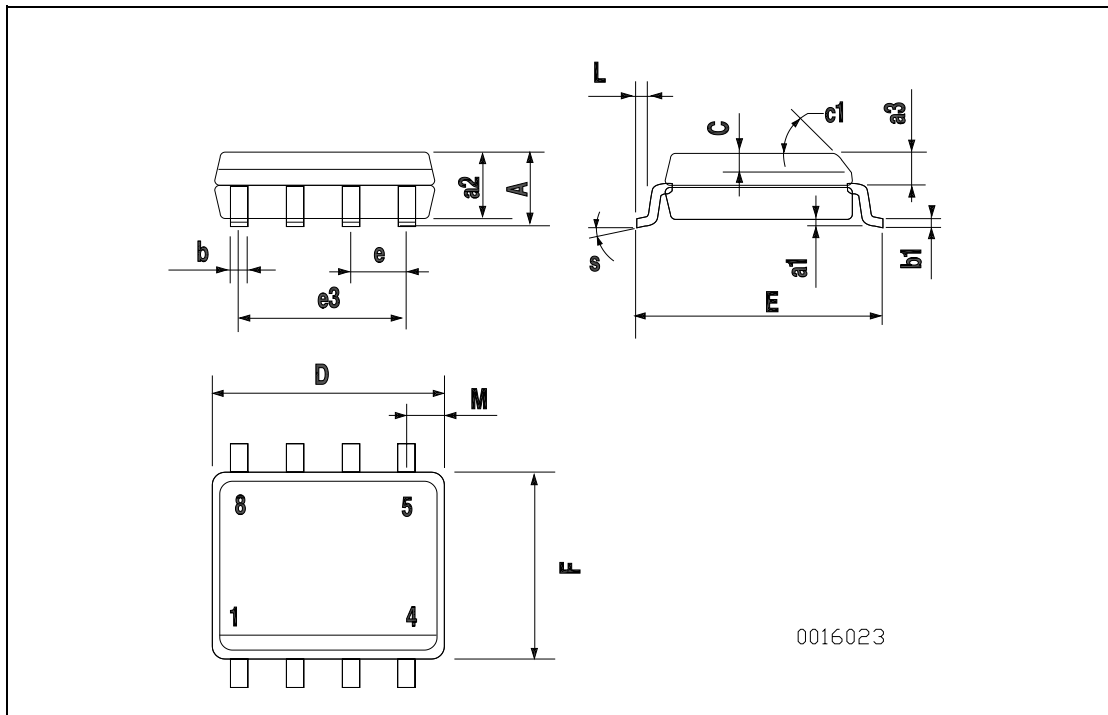


Table 12: Revision History

Date	Revision	Description of Changes
14-Dec-2004	1	First Revision

Obsolete Product(s) - Obsolete Product(s)

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